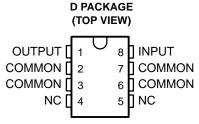
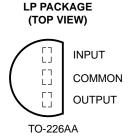
- 3-Terminal Regulators
- Output Current up to 100 mA
- No External Components
- Internal Thermal Overload Protection
- Internal Short-Circuit Current Limiting
- Direct Replacements for Fairchild μA78L00 Series

description

This series of fixed-voltage monolithic integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. In addition, they can be used with power-pass elements to make high-current voltage regulators. One of these regulators can deliver up to 100 mA of output current. The internal limiting and thermal shutdown features of



NC-No internal connection



these regulators make them essentially immune to overload. When used as a replacement for a zener diode-resistor combination, an effective improvement in output impedance can be obtained together with lower bias current.

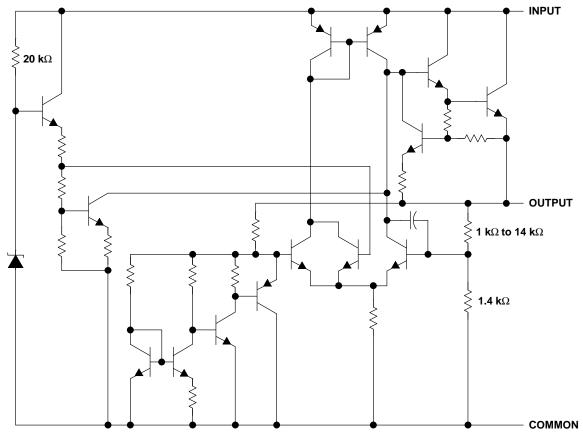
AVAILABLE OPTIONS

			PACKAGEI	DEVICES		
TJ	V _{O(nom)}	SMALL (PLASTIC CY (LI	_	CHIP FORM (Y)
	(V)		OUTPUT VOLTA	GE TOLERANCE		(1)
		5%	10%	5%	10%	
	2.6	μΑ78L02ACD	μΑ78L02CD	μΑ78L02ACLP	μΑ78L02CLP	μΑ78L02Y
	5	μΑ78L05ACD	μΑ78L05CD	μΑ78L05ACLP	μΑ78L05CLP	μΑ78L05Y
	6.2	μΑ78L06ACD	μΑ78L06CD	μΑ78L06ACLP	μΑ78L06CLP	μΑ78L06Y
0°C to 125°C	8	μΑ78L08ACD	μΑ78L08CD	μΑ78L08ACLP	μΑ78L08CLP	μΑ78L08Y
0 0 10 125 0	9	μΑ78L09ACD	μΑ78L09CD	μΑ78L09ACLP	μΑ78L09CLP	μΑ78L09Y
	10	μΑ78L10ACD	μΑ78L10CD	μΑ78L10ACLP	μΑ78L10CLP	μΑ78L10Y
	12	μΑ78L12ACD	μΑ78L12CD	μΑ78L12ACLP	μΑ78L12CLP	μΑ78L12Y
	15	μΑ78L15ACD	μΑ78L15CD	μΑ78L15ACLP	μΑ78L15CLP	μΑ78L15Y
-40°C to 125°C	5	μΑ78L05AQD	μΑ78L05QD	μΑ78L05QLP	μΑ78L05QLP	_
-40 C to 125°C	12	μΑ78L12AQD	μΑ78L12QD	μΑ78L12QLP	μΑ78L12QLP	_

D and LP packages are available taped and reeled. Add R suffix to device type (e.g., µA78L05ACDR).



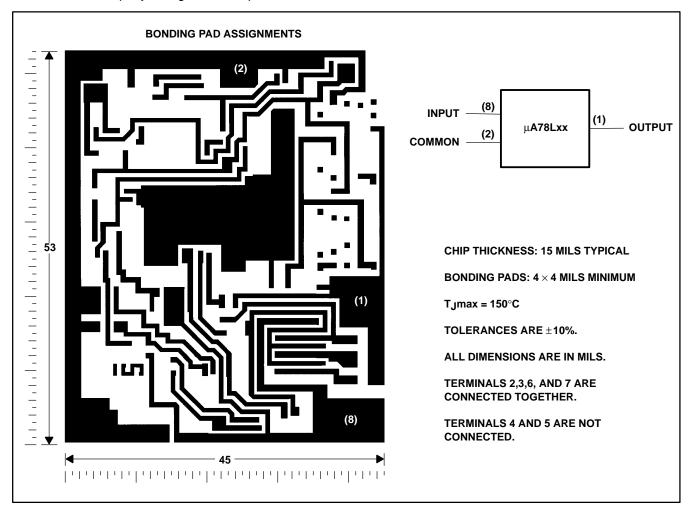
schematic



NOTE: Resistor values shown are nominal.

μΑ78LxxY chip information

These chips, when properly assembled, display characteristics similar to the μ A78LxxY. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chips may be mounted with conductive epoxy or a gold-silicon preform.



μΑ78LxxC absolute maximum ratings over operating temperature range (unless otherwise noted)

	μΑ78L02C, μΑ78L02AC THROUGH μΑ78L10C, μΑ78L10AC	μΑ78L12C, μΑ78L12AC μΑ78L15C, μΑ78L15AC	UNIT
Input voltage	30	35	V
Continuous total power dissipation (see Note 1)	See Dissipation	n Rating Tables	1 and 2
Operating free-air, T _A , case, T _C , or virtual junction, T _J , temperature range	0 to 125	0 to 125	°C
Storage temperature range, T _{Stg}	-65 to 150	-65 to 150	°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260	260	°C

To avoid exceeding the design maximum virtual junction temperature, these ratings should not be exceeded. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.

μΑ78LxxQ absolute maximum ratings over operating temperature range (unless otherwise noted)

	μ Α78L05Q , μ Α78L05AQ	μ A78L05AQ μ A78L12AQ		
Input voltage	30 35			
Continuous total power dissipation (see Note 1)	See Dissipation Rating Tables 1 and 2			
Operating free-air, T _A , case, T _C , or virtual junction, T _J , temperature range	-40 to 150	-40 to 150	°C	
Storage temperature range, T _{Stg}	-65 to 150	-65 to 150	°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260	260	°C	

NOTE 1: To avoid exceeding the design maximum virtual junction temperature, these ratings should not be exceeded. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.

DISSIPATION RATING TABLE 1 – FREE-AIR TEMPERATURE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	25°C	464 mW
LP†	775 mW	6.2 mW/°C	25°C	496 mW

 $[\]dagger$ The LP package dissipation rating is based on thermal resistance R $_{\theta JA}$ measured in still air with the device mounted in an Augat socket. The bottom of the package is 10 mm (0.375 in) above the socket.

DISSIPATION RATING TABLE 2 - CASE TEMPERATURE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _C	T _C = 125°C POWER RATING
D	1600 mW	19.6 mW/°C	65°C	424 mW
LP	1600 mW	28.6 mW/°C	94°C	713 mW



$\mu \text{A78L00 SERIES} \\ \text{POSITIVE-VOLTAGE REGULATORS} \\$

SLVS010E - JANUARY 1976 - REVISED JUNE 1997

recommended operating conditions

		MIN	MAX	UNIT
	μΑ78L02C, μΑ78L02AC	4.75	20	
	μΑ78L05C, μΑ78L05AC, μΑ78L05Q, μΑ78L05AQ	7	20	
	μΑ78L06C, μΑ78L06AC	8.5	20	
lanut voltage V	μΑ78L08C, μΑ78L08AC	10.5	23	V
Input voltage, V _I	μΑ78L09C, μΑ78L09AC	11.5	24	V
	μΑ78L10C, μΑ78L10AC	12.5	25	
	μΑ78L12C, μΑ78L12AC, μΑ78L12Q, μΑ78L12AQ	14.5	27	
	μΑ78L15C, μΑ78L15AC	17.5	30	
Output current, IO			100	mA
Operating virtual junction temporature, T.	μΑ78LxxC through μΑ78LxxAC	0	125	°C
Operating virtual junction temperature, T _J	μΑ78LxxQ and μΑ78LxxAQ	-40	125	C

electrical characteristics at specified virtual junction temperature, $V_I = 9 \text{ V}$, $I_O = 40 \text{ mA}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	- t	μ.	478L020	;	μ Α	78L02A	С	UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
		25°C	2.4	2.6	2.8	2.5	2.6	2.7		
Output voltage‡	$V_{I} = 4.75 \text{ V to } 20 \text{ V}, I_{O} = 1 \text{ mA to } 40 \text{ mA}$	F	2.35		2.85	2.45		2.75	V	
	I _O = 1 mA to 70 mA	Full range§	2.35		2.85	2.45		2.75		
Input voltage	V _I = 4.75 V to 20 V	25°C		20	125		20	100	mV	
regulation	V _I = 5 V to 20 V	25 C		16	100		16	75	IIIV	
Ripple rejection	V _I = 6 V to 20 V, f = 120 Hz	25°C	42	51		43	51		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		12	50		12	50	m∨	
regulation	I _O = 1 mA to 40 mA	25 0		6	25		6	25		
Output noise voltage	f = 10 Hz to 100 kHz	25°C		30			30		μV	
Dropout voltage		25°C		1.7			1.7		V	
Diag gurrant		25°C		3.6	6		3.6	6	A	
Bias current		125°C			5.5			5.5 mA		
Dies surrent shangs	V _I = 5 V to 20 V	Full rongs			2.5			2.5	4	
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA	

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T _J †	μ Α78L05C, μ Α78L05Q			μ Α ΄ μ Α	UNIT			
			MIN	TYP	MAX	MIN	TYP	MAX		
		25°C	4.6	5	5.4	4.8	5	5.2		
Output voltage‡	$V_1 = 7 \text{ V to } 20 \text{ V}, I_0 = 1 \text{ mA to } 40 \text{ mA}$	- "	4.5		5.5	4.75		5.25	V	
	$I_O = 1 \text{ mA to } 70 \text{ mA}$	Full range§	4.5		5.5	4.75		5.25		
Input voltage regulation	V _I = 7 V to 20 V	25°C		32	200		32	150	mV	
	V _I = 8 V to 20 V	25 C		26	150		26	100		
Ripple rejection	V _I = 8 V to 18 V, f = 120 Hz	25°C	40	49		41	49		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		15	60		15	60	mV	
regulation	I _O = 1 mA to 40 mA	25°C		8	30		8	30		
Output noise voltage	f = 10 Hz to 100 kHz	25°C		42			42		μV	
Dropout voltage		25°C		1.7			1.7		V	
Diag summent		25°C		3.8	6		3.8	6	A	
Bias current		125°C			5.5			5.5	mA	
Dies sument shanns	V _I = 8 V to 20 V	F			1.5			1.5		
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA	

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L02, μΑ78L02AC, μΑ78L05C, and μΑ78L05AC and –40°C to 125°C for μΑ78L05Q and μΑ78L05AQ.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L02, μΑ78L02AC, μΑ78L05C, and μΑ78L05AC and –40°C to 125°C for μΑ78L05Q and μΑ78L05AQ.

[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, V_I = 12 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.1	μΑ	478L06	С	μ Α	78L06A	C	UNIT	
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
		25°C	5.7	6.2	6.7	5.95	6.2	6.45		
Output voltage‡	$V_{I} = 8.5 \text{ V to } 20 \text{ V}, I_{O} = 1 \text{ mA to } 40 \text{ mA}$	5	5.6		6.8	5.9		6.5	V	
	I _O = 1 mA to 70 mA	Full range§	5.6		6.8	5.9		6.5		
Innut voltogo regulation	V _I = 8.5 V to 20 V	25°C		35	200		35	175	mV	
Input voltage regulation	V _I = 9 V to 20 V	25-0		29	150		29	125	IIIV	
Ripple rejection	V _I = 10 V to 20 V, f = 120 Hz	25°C	39	48		40	48		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		16	80		16	80	mV	
regulation	I _O = 1 mA to 40 mA	25 C		9	40		9	40		
Output noise voltage	f = 10 Hz to 100 kHz	25°C		46			46		μV	
Dropout voltage		25°C		1.7			1.7		V	
Diag gumant		25°C		3.9	6		3.9	6	A	
Bias current		125°C			5.5			5.5	mA	
Dies surrent change	V _I = 9 V to 20 V	Full rongs			1.5			1.5		
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA	

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	- +	μ /	478L08	С	μΑ	78L08A	C	UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	Olari	
		25°C	7.36	8	8.64	7.7	8	8.3		
Output voltage‡	$V_I = 10.5 \text{ V to } 23 \text{ V}, I_O = 1 \text{ mA to } 40 \text{ mA}$	- "	7.2		8.8	7.6		8.4	V	
	$I_O = 1 \text{ mA to } 70 \text{ mA}$	Full range§	7.2		8.8	7.6		8.4		
Innut voltage regulation	V _I = 10.5 V to 23 V	25°C		42	200		42	175	\/	
Input voltage regulation	V _I = 11 V to 23 V	25°C		36	150		36	125	m∨	
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	25°C	36	46		37	46		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		18	80		18	80	mV	
regulation	I _O = 1 mA to 40 mA	25°C		10	40		10	40		
Output noise voltage	f = 10 Hz to 100 kHz	25°C		54			54		μV	
Dropout voltage		25°C		1.7			1.7		V	
Diag gurrant		25°C		4	6		4	6	A	
Bias current		125°C			5.5			5.5	mA	
Bias current change	V _I = 5 V to 20 V	F			1.5			1.5	mA	
	I _O = 1 mA to 40 mA	Full range§			0.2			0.1		

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L06C, μΑ78L06AC, μΑ78L08C, and μΑ78L08AC.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L06C, μΑ78L06AC, μΑ78L08C, and μΑ78L08AC.

electrical characteristics at specified virtual junction temperature, V_I = 16 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.1	μ.	478L090	;	μ Α	78L09A	С	UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	ONIT	
		25°C	8.3	9	9.7	8.6	9	9.4		
Output voltage‡	$V_I = 12 \text{ V to } 24 \text{ V}, I_O = 1 \text{ mA to } 40 \text{ mA}$	5	8.1		9.9	8.55		9.45	V	
	$I_O = 1 \text{ mA to } 70 \text{ mA}$	Full range§	8.1		9.9	8.55		9.45		
Input voltage regulation	V _I = 12 V to 24 V	25°C		45	225		45	175	mV	
	V _I = 13 V to 24 V	25 C		40	175		40	125	IIIV	
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	25°C	36	45		38	45		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		19	90		19	90	mV	
regulation	I _O = 1 mA to 40 mA	25 0		11	40		11	40	IIIV	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		58			58		μV	
Dropout voltage		25°C		1.7			1.7		V	
Dies surrent		25°C		4.1	6		4.1	6	A	
Bias current		125°C			5.5			5.5	mA	
Dies surrent change	V _I = 13 V to 24 V	Full ronge &			1.5			1.5		
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA	

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.†	μ.	478L100	;	μ Α	78L10A	С	UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	ONIT	
		25°C	9.2	10	10.8	9.6	10	10.4		
Output voltage‡	$V_I = 13 \text{ V to } 25 \text{ V}, I_O = 1 \text{ mA to } 40 \text{ mA}$		9		11	9.5		10.5	V	
	I _O = 1 mA to 70 mA	Full range§	9		11	9.5		10.5		
Input voltage regulation	V _I = 13 V to 25 V	25°C		51	225		51	175	mV	
	V _I = 14 V to 25 V	25°C		42	175		42	125	IIIV	
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	25°C	36	44		37	44		dB	
Output voltage	I _O = 1 mA to 100 mA	25°C		20	90		20	90	mV	
regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	25 C		11	40		11	40	IIIV	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		62			62		μV	
Dropout voltage		25°C		1.7			1.7		V	
Bias current		25°C		4.2	6		4.2	6	mA	
bias current		125°C			5.5			5.5	IIIA	
Dies surrent shangs	V _I = 14 V to 25 V	F			1.5			1.5		
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA	

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L09C, μΑ78L09AC, μΑ78L10C, and μΑ78L10AC.

[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L09C, μΑ78L09AC, μΑ78L10C, and μΑ78L10AC.

electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TJ [†]	μ Α78L12C, μ Α78L12Q			μ Α78L12AC, μ Α78L12AQ			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
		25°C	11.1	12	12.9	11.5	12	12.5	
Output voltage‡	$V_{I} = 14 \text{ V to } 27 \text{ V}, I_{O} = 1 \text{ mA to } 40 \text{ mA}$	- " 8	10.8		13.2	11.4		12.6	V
	I _O = 1 mA to 70 mA	Full range§	10.8		13.2	11.4		12.6	
Input voltage	V _I = 14.5 V to 27 V	25°C		55	250		55	250	-l m∨
regulation	V _I = 16 V to 27 V			49	200		49	200	
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	25°C	36	42		37	42		dB
Output voltage	I _O = 1 mA to 100 mA	0500		22	100		22	100	\/
regulation	I _O = 1 mA to 40 mA	25°C		13	50		13	50	mV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		70			70		μV
Dropout voltage		25°C		1.7			1.7		V
D'an annual		25°C		4.3	6.5		4.3	6.5	^
Bias current	as current 125°C			6		-	6	mA	
Dies summent about to	V _I = 16 V to 27 V	F			1.5			1.5	A
Bias current change	I _O = 1 mA to 40 mA	Full range§			0.2			0.1	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.+	μ	A78L150	;	μ Α	78L15A	С	UNIT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	MIN	TYP	MAX	UNII
		25°C	13.8	15	16.2	14.4	15	15.6	
Output voltage‡	$V_{I} = 17.5 \text{ V to } 30 \text{ V}, \qquad I_{O} = 1 \text{ mA to } 40 \text{ mA}$	F	13.5		16.5	14.25		15.75	V
	I _O = 1 mA to 70 mA	Full range§	13.5		16.5	14.25		15.75	
Input voltage	V _I = 17.5 V to 30 V	2500		65	300		65	300	mV
regulation	V _I = 20 V to 30 V	25°C		58	250		58	250] ""
Ripple rejection	V _I = 18.5 V to 28.5 V, f = 120 Hz	25°C	33	39		34	39		dB
Output voltage	I _O = 1 mA to 100 mA	0500		25	150		25	150	
regulation	I _O = 1 mA to 40 mA	25°C		15	75		15	75	mV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		82			82		μV
Dropout voltage		25°C		1.7			1.7		V
D'a a summant		25°C		4.6	6.5		4.6	6.5	Δ
Bias current		125°C			6			6	mA
Bias current	V _I = 10 V to 30 V	F!!			1.5			1.5	A
change	I _O = 1 mA to 40 mA	Full range ^s			0.2			0.1	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L12C, μΑ78L12AC, μΑ78L15C, and μΑ78L15AC.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for μΑ78L12C, μΑ78L12AC, μΑ78L15C, and μΑ78L15AC.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 9 \text{ V}$, $I_O = 40 \text{ mA}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ Α	UNIT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNII
Output voltage‡			2.6		V
I input voltage regulation	V _I = 4.75 V to 20 V	20			mV
	V _I = 5 V to 20 V		IIIV		
Ripple rejection	$V_I = 6 \text{ V to } 20 \text{ V}, f = 120 \text{ Hz}$		51		dB
Output voltage regulation	I _O = 1 mA to 100 mA		12		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		6		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		30		μV
Dropout voltage			1.7		V
Bias current			3.6		mA

TPulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a $0.33-\mu F$ capacitor across the input and a $0.1-\mu F$ capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 10 \text{ V}$, $I_O = 40 \text{ mA}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ Α	UNIT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage [‡]			5		V
Input voltage regulation	V _I = 7 V to 20 V			mV	
	V _I = 8 V to 20 V		IIIV		
Ripple rejection	$V_I = 8 V \text{ to } 18 V, f = 120 Hz$		49		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		15		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		8		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		42		μV
Dropout voltage			1.7		V
Bias current			3.8		mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a $0.33-\mu F$ capacitor across the input and a $0.1-\mu F$ capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 12 V, I_O = 40 mA, T_A = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ.	UNIT		
	TEST CONDITIONS!	MIN	TYP	MAX	UNIT
Output voltage [‡]			6.2		V
I Input voltage regulation	V _I = 8.5 V to 20 V			mV	
	V _I = 9 V to 20 V			IIIV	
Ripple rejection	$V_I = 10 \text{ V to } 20 \text{ V}, f = 120 \text{ Hz}$		48		dB
Output voltage regulation	I _O = 1 mA to 100 mA		16		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		9		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		46		μV
Dropout voltage			1.7		V
Bias current			3.9		mA

[†] Pulse-testing techniques maintain T, as close to TA as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 14 \text{ V}$, $I_O = 40 \text{ mA}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ Α	UNIT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage‡			8		V
Input voltage regulation	V _I = 10.5 V to 23 V	42			mV
	V _I = 11 V to 23 V			1117	
Ripple rejection	$V_I = 13 \text{ V to } 23 \text{ V}, f = 120 \text{ Hz}$		46		dB
Output voltage regulation	I _O = 1 mA to 100 mA		18		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		10		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		54		μV
Dropout voltage			1.7		V
Bias current			4	, and the second	mA

The Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 16 \text{ V}$, $I_O = 40 \text{ mA}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ	LINUT		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage [‡]			9		V
Input voltage regulation	V _I = 12 V to 24 V	45			mV
	V _I = 13 V to 24 V		1110		
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz		45		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		19		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	11			IIIV
Output noise voltage	f = 10 Hz to 100 kHz		58		μV
Dropout voltage			1.7		V
Bias current			4.1		mA

The Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 14 \text{ V}$, $I_O = 40 \text{ mA}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ Α	UNIT		
PARAMETER	TEST CONDITIONS!	MIN	TYP	MAX	UNIT
Output voltage‡			10		V
Input voltage regulation	V _I = 13 V to 25 V	51			mV
	V _I = 14 V to 25 V			1117	
Ripple rejection	$V_I = 15 \text{ V to } 25 \text{ V}, f = 120 \text{ Hz}$		44		dB
Output voltage regulation	I _O = 1 mA to 100 mA		20		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		11		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		62		μV
Dropout voltage			1.7		V
Bias current			4.2		mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.



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electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 40 mA, T_A = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Δ	UNIT		
PARAMETER	1EST CONDITIONS	MIN	TYP	MAX	UNII
Output voltage‡			12		V
Input voltage regulation	V _I = 14.5 V to 27 V			mV	
	V _I = 16 V to 27 V		IIIV		
Ripple rejection	$V_I = 15 \text{ V to } 25 \text{ V}, f = 120 \text{ Hz}$		42		dB
Output voltage regulation	I _O = 1 mA to 100 mA		22		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		13		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		70		μV
Dropout voltage			1.7	, and the second	V
Bias current			4.3		mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 40 mA, T_A = 25°C (unless otherwise noted)

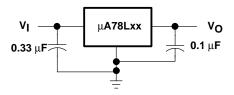
PARAMETER	TEST CONDITIONS†	μ.	UNIT		
PARAMETER	TEST CONDITIONS:	MIN	TYP	MAX	UNII
Output voltage [‡]			15		V
Input voltage regulation	$V_{I} = 17.5 \text{ V to } 30 \text{ V}$			mV	
	$V_I = 20 \text{ V to } 30 \text{ V}$		IIIV		
Ripple rejection	$V_I = 18.5 \text{ V to } 28.5 \text{ V}, f = 120 \text{ Hz}$		39		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		25		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	15			IIIV
Output noise voltage	f = 10 Hz to 100 kHz		82		μV
Dropout voltage			1.7		V
Bias current			4.6	·	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

APPLICATION INFORMATION

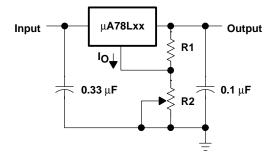


 $+ \underbrace{\begin{array}{c|c} IN \\ V_I \\ - \end{array}}_{\text{COM}} \underbrace{\begin{array}{c|c} \mu A78Lxx \\ \hline \hline i_L \end{array}}_{\text{OUT}} G$

Figure 1. Fixed Output Regulator

Figure 2. Positive Regulator in Negative

Configuration (VI Must Float)



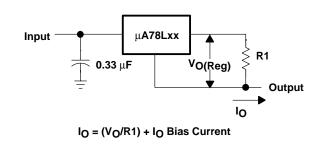


Figure 3. Adjustable Output Regulator

Figure 4. Current Regulator

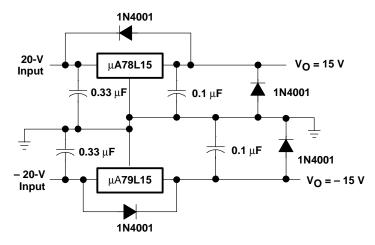


Figure 5. Regulated Dual Supply

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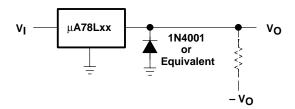


Figure 6. Output Polarity-Reversal Protection Circuit

operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground but instead is connected to a voltage source of opposite polarity (e.g., operational amplifiers, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 6. This protects the regulator from output polarity reversals during startup and short-circuit operation.

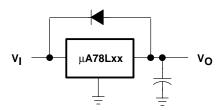


Figure 7. Reverse-Bias Protection Circuit

reverse-bias protection

Occasionally, there exists the possibility that the input voltage to the regulator can collapse faster than the output voltage. This could occur, for example, when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be employed as shown in Figure 7.



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